20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A. **M.IF150**



Complementary Silicon Plastic Power Transistors

Designed for use as high-frequency drivers in audio amplifiers.

Features

• DC Current Gain Specified to 5.0 Amperes

$$h_{FE} = 70 \text{ (Min)} @ I_C = 0.5 \text{ Add}$$

- $= 10 (Min) @ I_C = 2.0 Adc$
- Collector-Emitter Sustaining Voltage –
 V_{CEO(sus)} = 250 Vdc (Min) MJE15032, MJE15033
- High Current Gain Bandwidth Product
- $f_T = 30 \text{ MHz} (\text{Min}) @ I_C = 500 \text{ mAdc}$
- TO-220AB Compact Package
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Machine Model C Human Body Model 3B

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|-----------------------------------|-----------------|-----------|
| Collector-Emitter Voltage | V _{CEO} | 250 | Vdc |
| Collector-Base Voltage | V _{CB} | 250 | Vdc |
| Emitter-Base Voltage | V _{EB} | 5.0 | Vdc |
| Collector Current – Continuous – Peak | lc | 8.0 16 | Adc |
| Base Current | I _B | 2.0 | Adc |
| Total Power Dissipation @ T _C = 25°C Derate above 25°C | PD | 50 0.40 | W W/°C |
| Total Power Dissipation @ T _A = 25°C Derate above 25°C | P _D | 2.0 0.016 | W W/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | −65 to + 150 | °C |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Мах | Unit |
|--|------------------|------|------|
| Thermal Resistance, Junction-to-Case | R _{θJC} | 2.5 | °C/W |
| Thermal Resistance, Junction-to-Ambient | R _{θJA} | 62.5 | °C/W |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

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8.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 250 VOLTS, 50 WATTS





MJE15032 (NPN), MJE15033 (PNP)

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|--|-----------------------|----------------|-----|------|
| OFF CHARACTERISTICS | | | | |
| Collector-Emitter Sustaining Voltage (Note 1) ($I_C = 10 \text{ mAdc}, I_B = 0$) | V _{CEO(sus)} | 250 | - | Vdc |
| Collector Cutoff Current ($V_{CB} = 250 \text{ Vdc}, I_E = 0$) | I _{CBO} | - | 10 | μAdc |
| Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_C = 0$) | I _{EBO} | - | 10 | μAdc |
| ON CHARACTERISTICS (Note 1) | | | | |
| DC Current Gain ($I_C = 0.5 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 1.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 2.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc}$) | hfe | 70 50 10 | | - |
| Collector-Emitter Saturation Voltage $(I_C = 1.0 \text{ Adc}, I_B = 0.1 \text{ Adc})$ | V _{CE(sat)} | - | 0.5 | Vdc |
| Base-Emitter On Voltage ($I_C = 1.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc}$) | V _{BE(on)} | - | 1.0 | Vdc |
| DYNAMIC CHARACTERISTICS | | | | |
| Current Gain – Bandwidth Product (Note 2) ($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc, $f_{test} = 1.0$ MHz) | fT | 30 | - | MHz |
| $\mathbf{T} = \mathbf{T} + \mathbf{D} + \mathbf{T} + $ | | | | |

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%. 2. $f_T = |h_{fe}| \bullet f_{test}$.

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